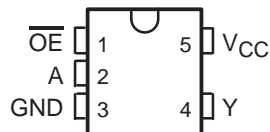


SN74LVC1G125 SINGLE BUS BUFFER GATE WITH 3-STATE OUTPUTS

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- **EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **I_{off} Feature Supports Partial-Power-Down Mode Operation**
- **Supports 5-V V_{CC} Operation**
- **Package Options Include Plastic Small-Outline Transistor (DBV, DCK) Packages**

DBV OR DCK PACKAGE
(TOP VIEW)



description

This bus buffer gate is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC1G125 features a single line driver with a 3-state output. The output is disabled when the output-enable (\overline{OE}) input is high.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The SN74LVC1G125 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

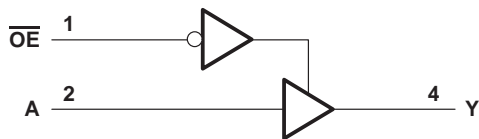
INPUTS		OUTPUT
\overline{OE}	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



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PRODUCT PREVIEW

SN74LVC1G125

SINGLE BUS BUFFER GATE

WITH 3-STATE OUTPUTS

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	–0.5 V to 6.5 V
Input voltage range, V_I (see Note 1)	–0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2)	–0.5 V to $V_{CC} + 0.5$ V
Input clamp current, I_{IK} ($V_I < 0$)	–50 mA
Output clamp current, I_{OK} ($V_O < 0$)	–50 mA
Continuous output current, I_O	±50 mA
Continuous current through V_{CC} or GND	±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DBV package	347°C/W
DCK package	389°C/W
Storage temperature range, T_{stg}	–65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 2. The value of V_{CC} is provided in the recommended operating conditions table.
 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

		MIN	MAX	UNIT	
V_{CC}	Supply voltage	Operating	1.65	5.5	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	$V_{CC} = 1.65$ V to 1.95 V	$0.65 \times V_{CC}$	V	
		$V_{CC} = 2.3$ V to 2.7 V	1.7		
		$V_{CC} = 3$ V to 3.6 V	2		
		$V_{CC} = 4.5$ V to 5.5 V	$0.7 \times V_{CC}$		
V_{IL}	Low-level input voltage	$V_{CC} = 1.65$ V to 1.95 V	$0.35 \times V_{CC}$	V	
		$V_{CC} = 2.3$ V to 2.7 V	0.7		
		$V_{CC} = 3$ V to 3.6 V	0.8		
		$V_{CC} = 4.5$ V to 5.5 V	$0.3 \times V_{CC}$		
V_I	Input voltage	0	5.5	V	
V_O	Output voltage	0	V_{CC}	V	
I_{OH}	High-level output current	$V_{CC} = 1.65$ V	–4	mA	
		$V_{CC} = 2.3$ V	–8		
		$V_{CC} = 3$ V	–16		
		$V_{CC} = 4.5$ V	–32		
I_{OL}	Low-level output current	$V_{CC} = 1.65$ V	4	mA	
		$V_{CC} = 2.3$ V	8		
		$V_{CC} = 3$ V	16		
		$V_{CC} = 4.5$ V	32		
$\Delta t/\Delta v$	Input transition rise or fall rate	$V_{CC} = 1.8$ V ± 0.15 V, 2.5 V ± 0.2 V	20	ns/V	
		$V_{CC} = 3.3$ V ± 0.3 V	10		
		$V_{CC} = 5$ V ± 0.5 V	5		
T_A	Operating free-air temperature	–40	85	°C	

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V _{CC}	MIN	TYP†	MAX	UNIT
V _{OH}		I _{OH} = -100 μA	1.65 V to 5.5 V	V _{CC} -0.1			V
		I _{OH} = -4 mA	1.65 V	1.2			
		I _{OH} = -8 mA	2.3 V	1.9			
		I _{OH} = -16 mA	3 V	2.4			
		I _{OH} = -24 mA		2.3			
		I _{OH} = -32 mA	4.5 V	3.8			
V _{OL}		I _{OL} = 100 μA	1.65 V to 5.5 V			0.1	V
		I _{OL} = 4 mA	1.65 V			0.45	
		I _{OL} = 8 mA	2.3 V			0.3	
		I _{OL} = 16 mA	3 V			0.4	
		I _{OL} = 24 mA				0.55	
		I _{OL} = 32 mA	4.5 V			0.55	
I _I	A or $\overline{\text{OE}}$ inputs	V _I = 5.5 V or GND	0 to 5.5 V			±5	μA
I _{off}		V _I or V _O = 5.5 V	0			±10	μA
I _{OZ}		V _O = 0 to 5.5 V	3.6 V			10	μA
I _{CC}		V _I = 5.5 V or GND, I _O = 0	1.65 V to 5.5 V			10	μA
ΔI _{CC}		One input at V _{CC} - 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V			500	μA
C _i		V _I = V _{CC} or GND	3.3 V				pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 4)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A	Y									ns
t _{en}	$\overline{\text{OE}}$	Y									ns
t _{dis}	$\overline{\text{OE}}$	Y									ns

operating characteristics, T_A = 25°C

PARAMETER	TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT
		TYP	TYP	TYP	TYP	
C _{pd} Power dissipation capacitance	f = 10 MHz					pF

PRODUCT PREVIEW

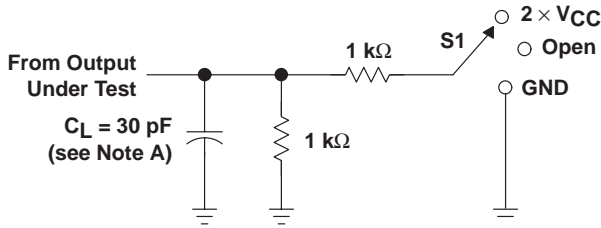


SN74LVC1G125
SINGLE BUS BUFFER GATE
WITH 3-STATE OUTPUTS

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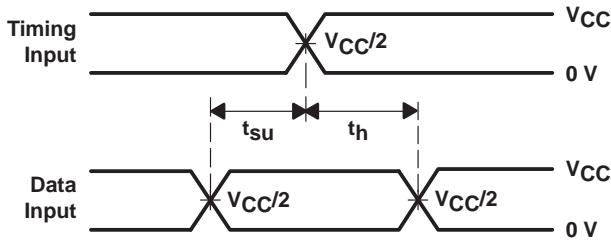
PARAMETER MEASUREMENT INFORMATION

$V_{CC} = 1.8\text{ V} \pm 0.15\text{ V}$

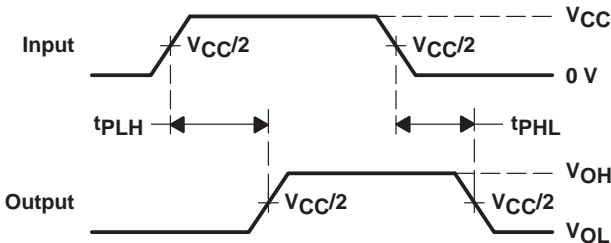


LOAD CIRCUIT

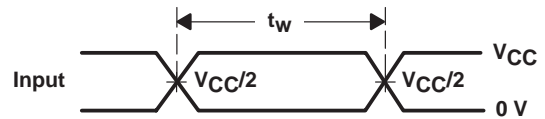
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	$2 \times V_{CC}$
t_{PHZ}/t_{PZH}	GND



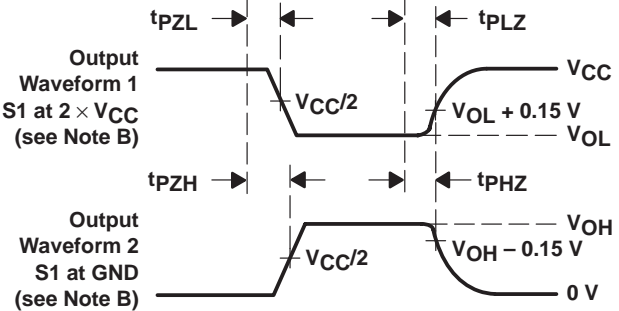
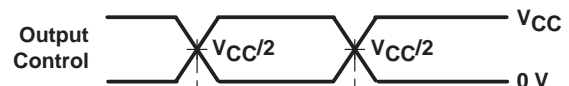
**VOLTAGE WAVEFORMS
 SETUP AND HOLD TIMES**



**VOLTAGE WAVEFORMS
 PROPAGATION DELAY TIMES**



**VOLTAGE WAVEFORMS
 PULSE DURATION**



**VOLTAGE WAVEFORMS
 ENABLE AND DISABLE TIMES**

- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 2\text{ ns}$, $t_f \leq 2\text{ ns}$.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .

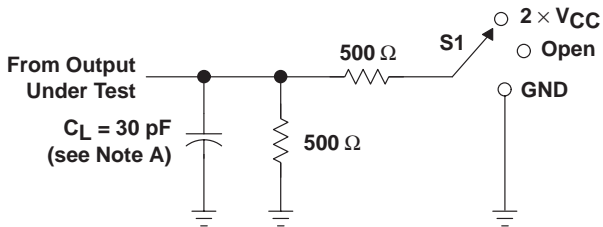
Figure 1. Load Circuit and Voltage Waveforms

PRODUCT PREVIEW



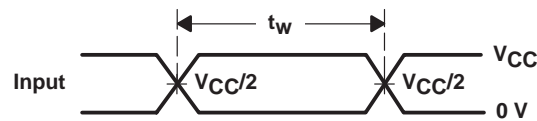
PARAMETER MEASUREMENT INFORMATION

$V_{CC} = 2.5\text{ V} \pm 0.2\text{ V}$

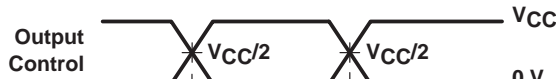
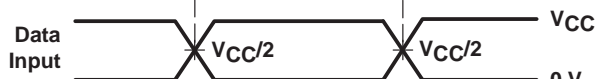


LOAD CIRCUIT

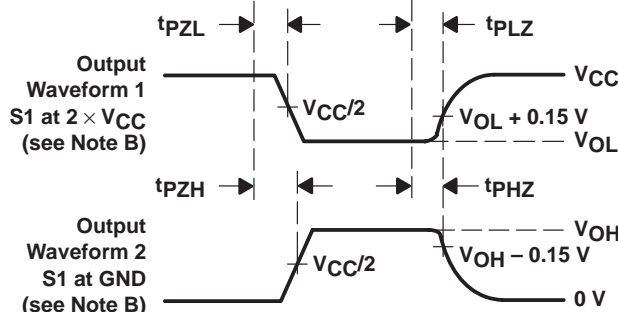
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 $\times V_{CC}$
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

- NOTES: A. C_L includes probe and jig capacitance.
 B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 C. All input pulses are supplied by generators having the following characteristics: PRR $\leq 10\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 2\text{ ns}$, $t_f \leq 2\text{ ns}$.
 D. The outputs are measured one at a time with one transition per measurement.
 E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 F. t_{PZL} and t_{PZH} are the same as t_{en} .
 G. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 2. Load Circuit and Voltage Waveforms

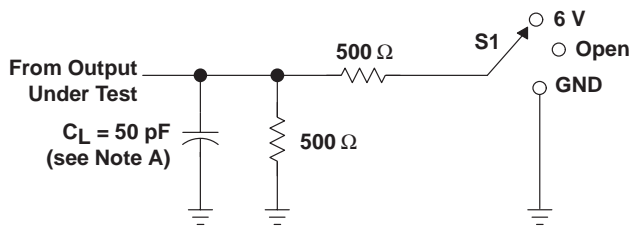
PRODUCT PREVIEW

SN74LVC1G125 SINGLE BUS BUFFER GATE WITH 3-STATE OUTPUTS

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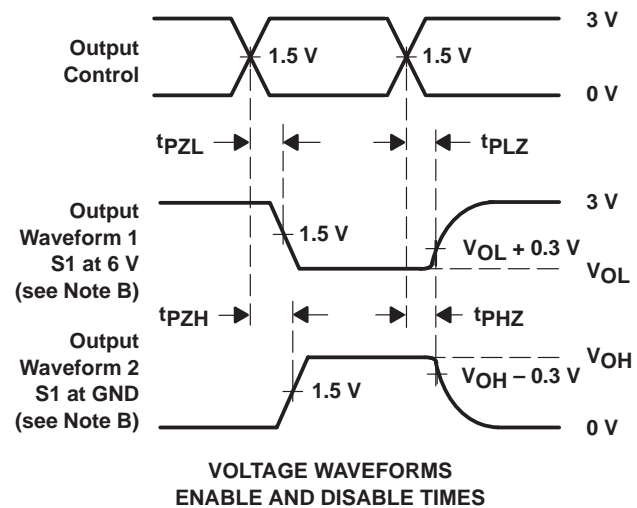
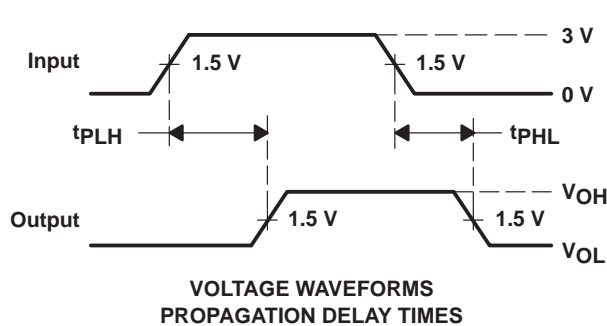
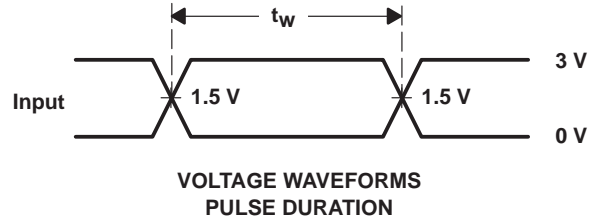
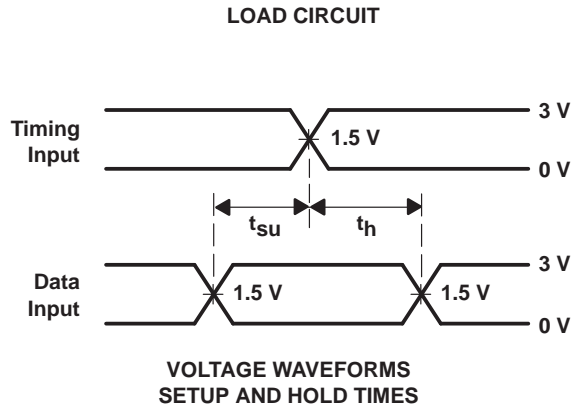
PARAMETER MEASUREMENT INFORMATION

$$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$$



LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

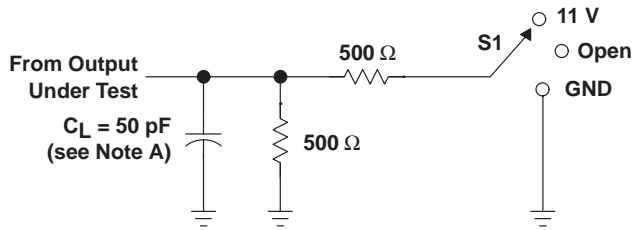


- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2.5 \text{ ns}$, $t_f \leq 2.5 \text{ ns}$.
 - The outputs are measured one at a time with one transition per measurement.
 - t_{PZL} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{en} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 3. Load Circuit and Voltage Waveforms

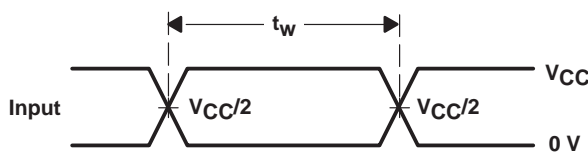
PARAMETER MEASUREMENT INFORMATION

$V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

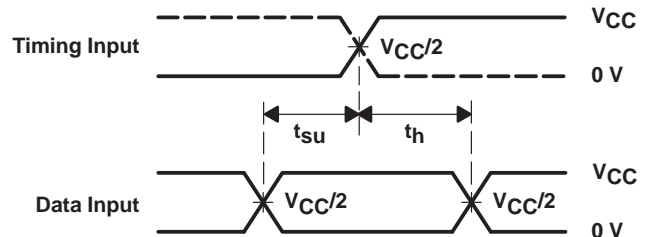


LOAD CIRCUIT

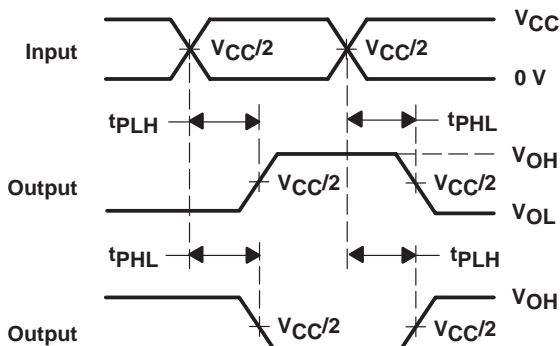
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	11 V
t_{PHZ}/t_{PZH}	GND



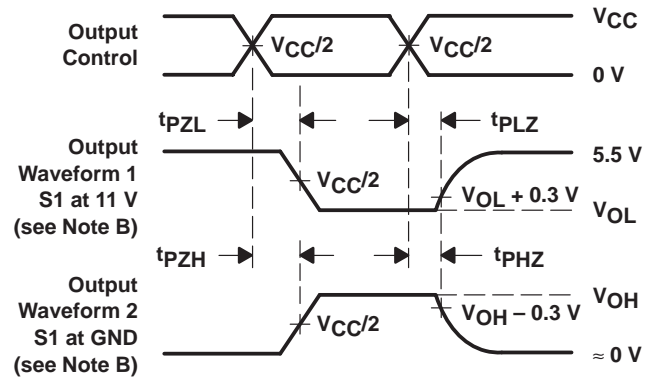
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

- NOTES: A. C_L includes probe and jig capacitance.
 B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 2.5\text{ ns}$, $t_f \leq 2.5\text{ ns}$.
 D. The outputs are measured one at a time with one transition per measurement.
 E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 F. t_{PZL} and t_{PZH} are the same as t_{en} .
 G. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 4. Load Circuit and Voltage Waveforms

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